

Graphene based superconducting circuits platform

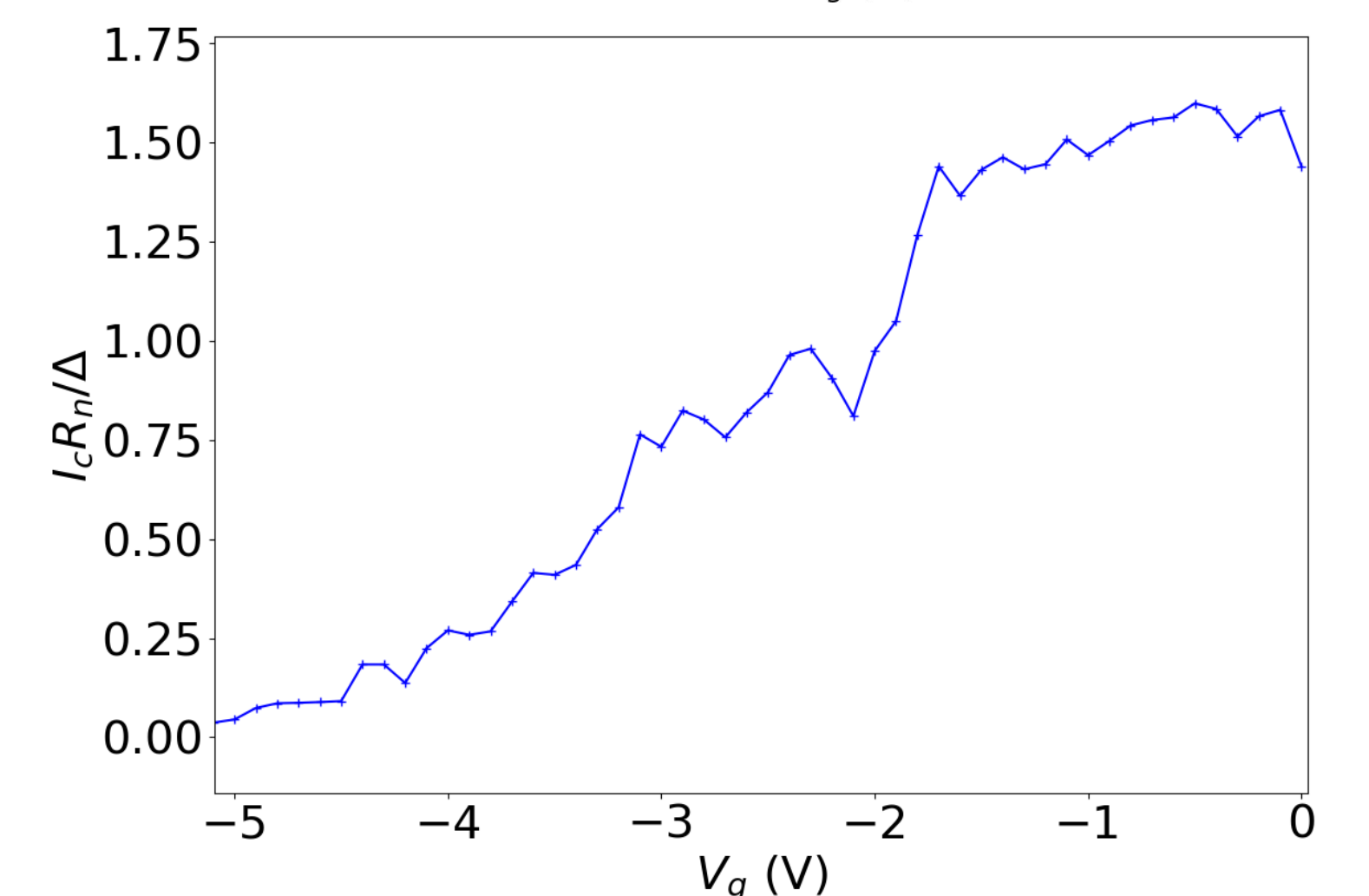
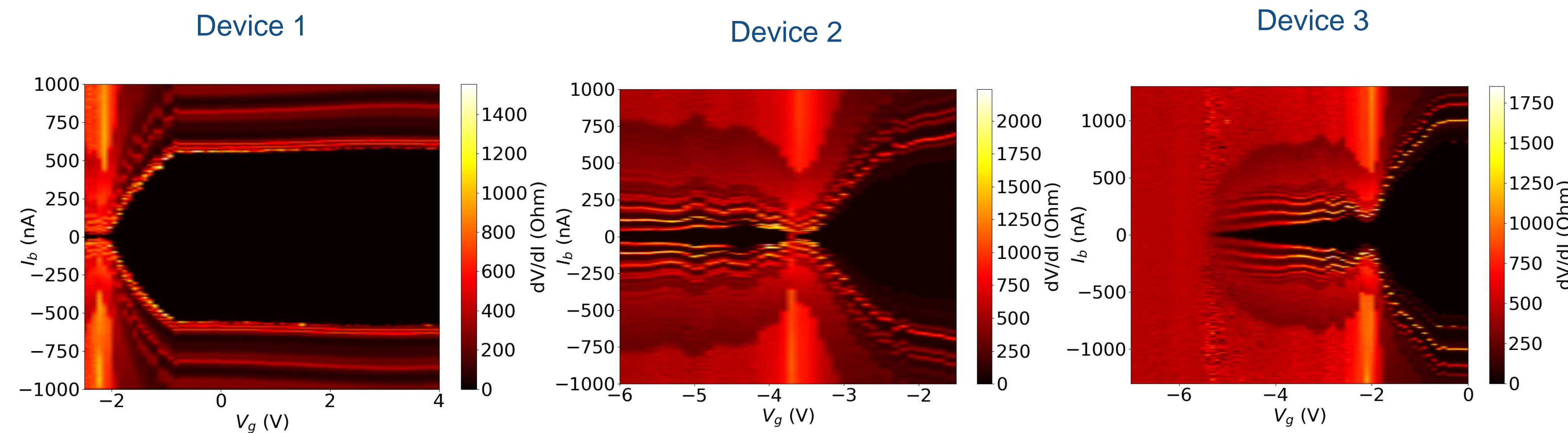
G.Butseraen¹, K.Watanabe²,
T.Taniguchi², F.Lefloch³, J.Renard¹

1: Hybrid systems at low dimensions, Univ. Grenoble Alpes, CNRS, Grenoble INP, Institut Néel, 38000 Grenoble, France
2: National Institute for Materials Science, Tsukuba, 305-0044, Japan
3: CEA, INAC-PHELIQS, F-38054 Grenoble, France

Motivation

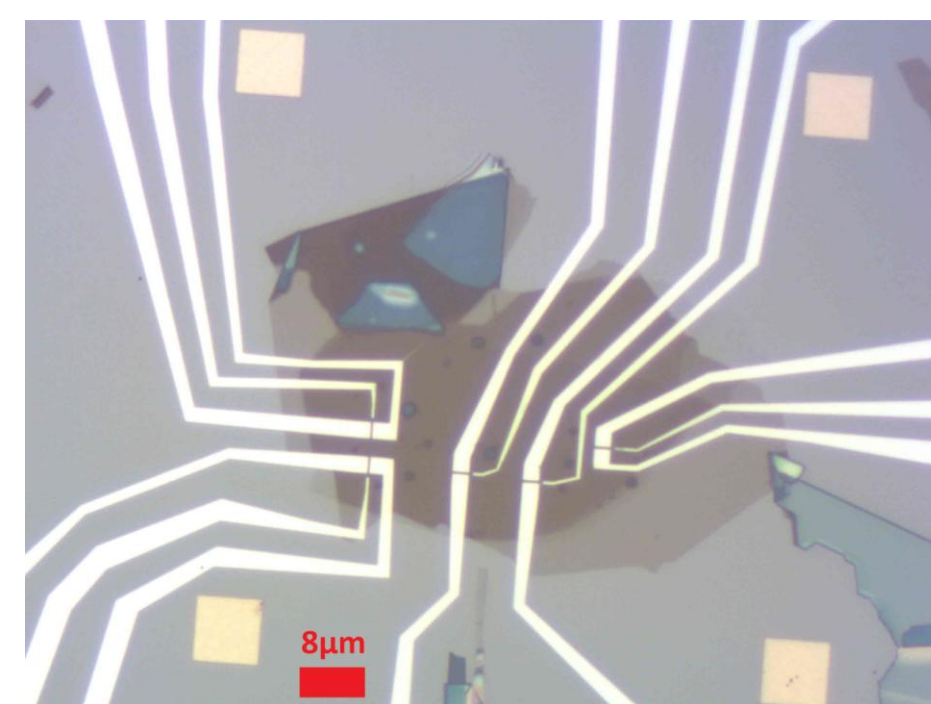
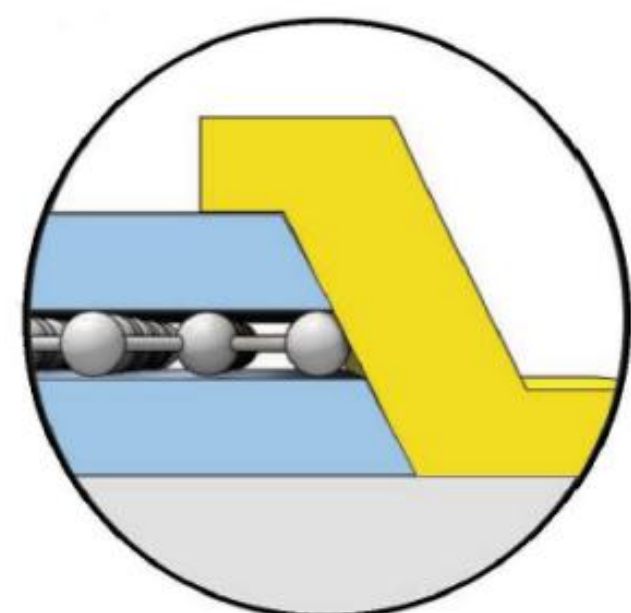
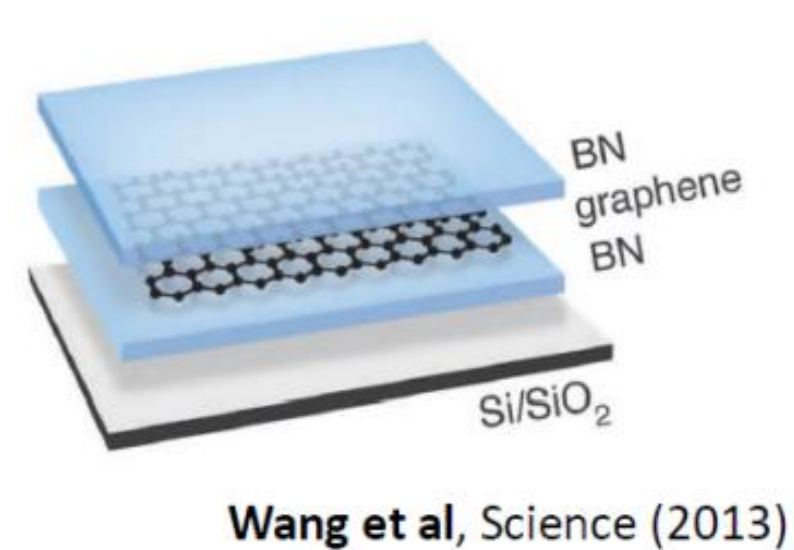
- Gate tunable material
- A lot of junction regimes accessible
- Interplay between superconductivity and relativistic quantum mechanics
- Easy to integrate in RF circuits

Ti/Al junctions critical current



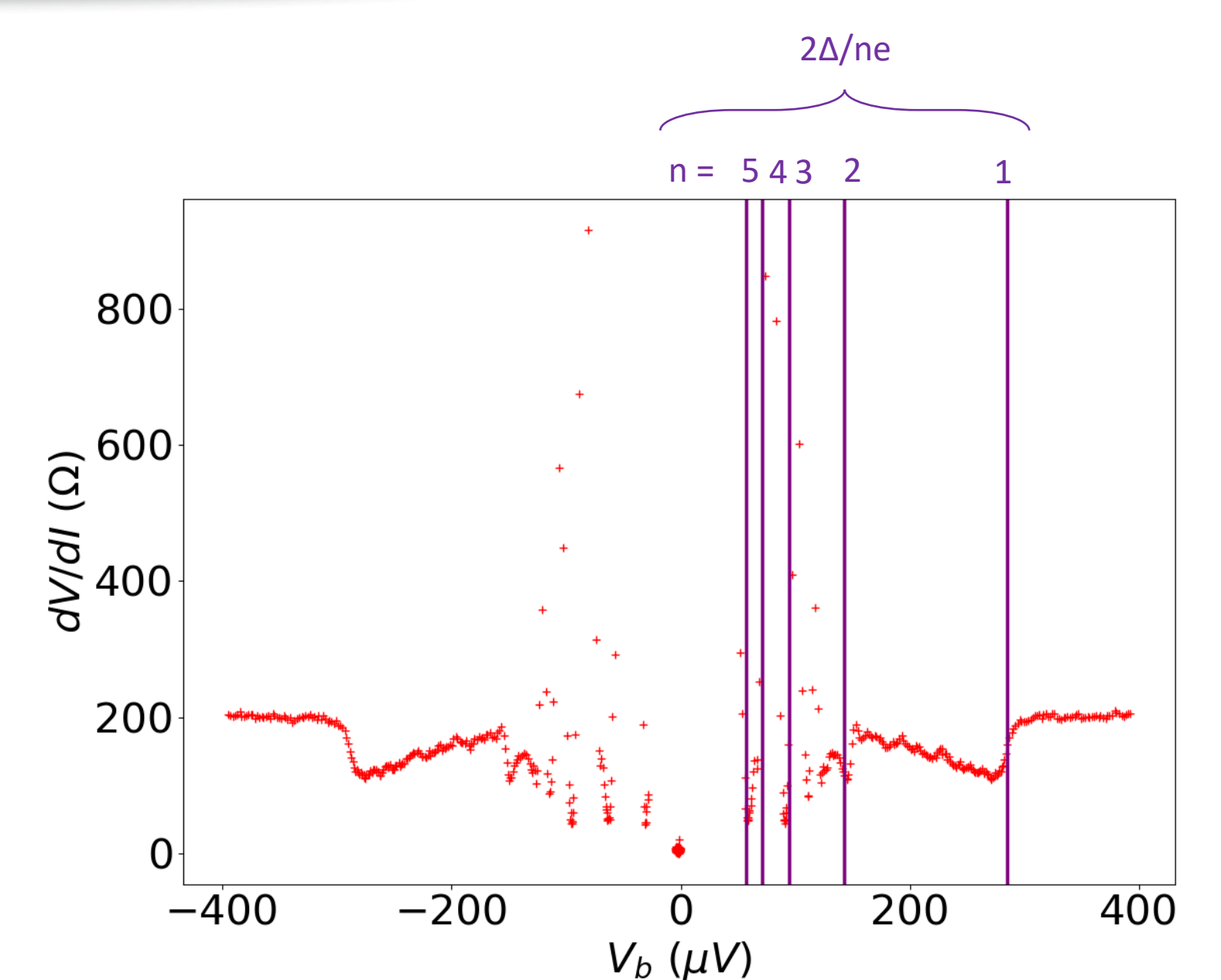
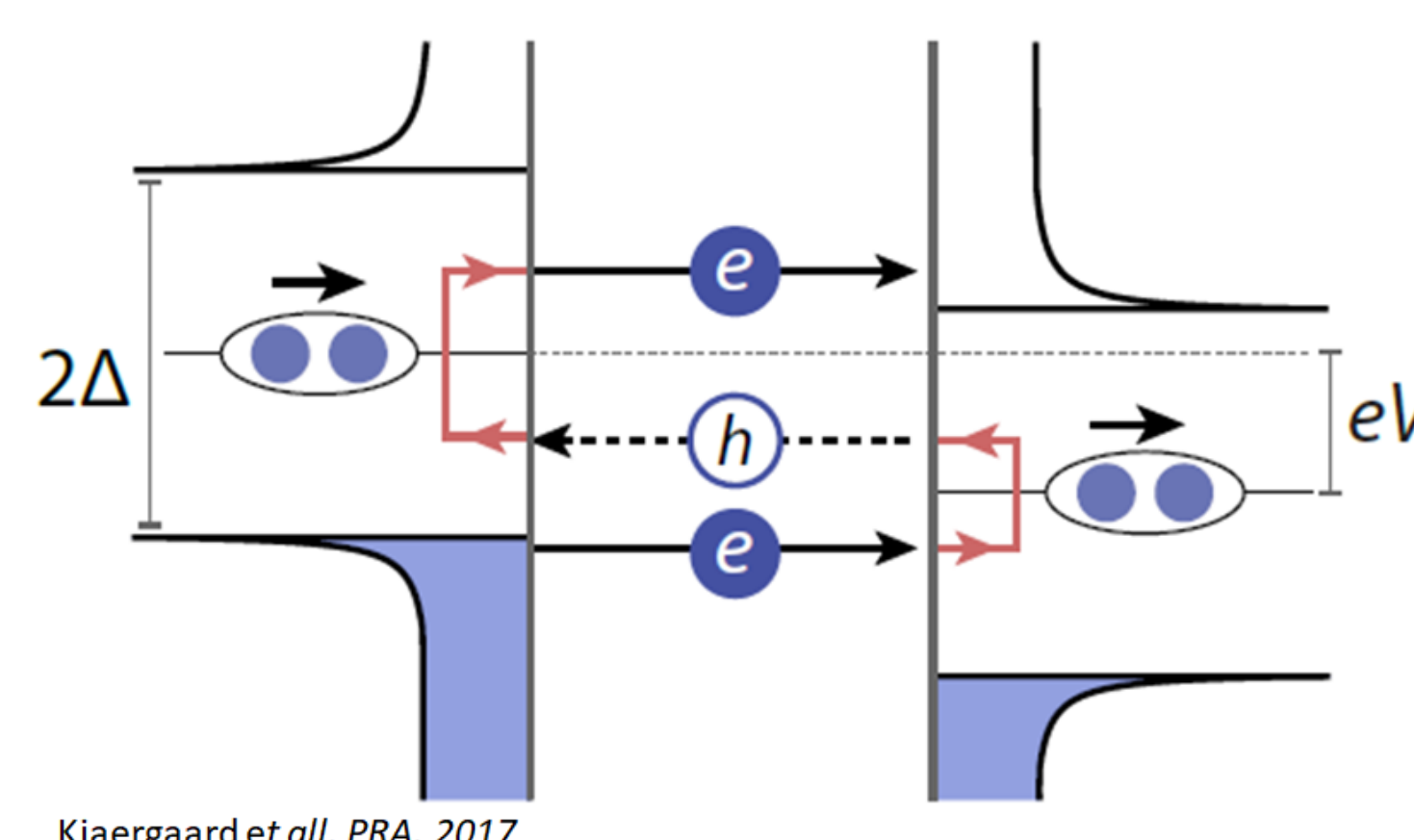
Fabrication and measurement setup

- Encapsulated graphene [1]
- Junction size: $W = 2\mu\text{m}$, $L = 300\text{nm}$
- Superconducting contact: Ti/Al or MoGe
- Intrinsic Si substrate
- Side gate control of the carrier density
- Standard 2 probes current bias lockin measurement technique at a base temperature of 100mK



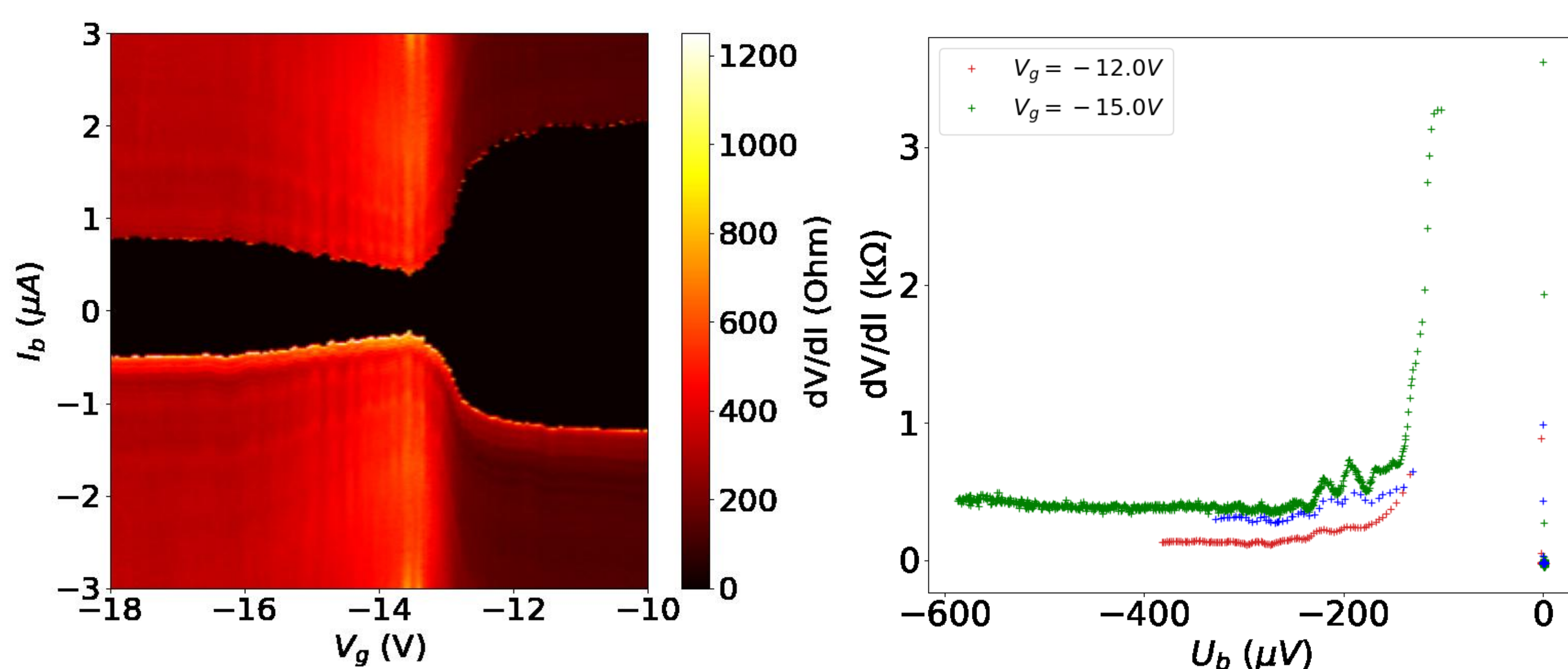
- Extracted induced gap: $\Delta = 140\mu\text{eV}$
- Critical current close to the tunnel junction limit $2\Delta/R_N e$
- Critical current effectively tunable with a side gate

Ti/Al junctions multiple Andreev reflections (MAR)



- MAR should manifest themselves as peaks in conductance for $V_b = 2\Delta/ne$ with n an integer
- Sharp peaks in resistance are observed whereas only peaks in the conductance are expected
- Some peaks in conductance do not correspond to the $2\Delta/ne$ formula

MoGe junctions



- Critical current up to $2\mu\text{A}$ despite local gating
- MAR have a more standard behavior in contrast with the Ti/Al devices where sharp peaks in resistance are measured

Conclusion

- The side gate technology offers a 'non invasive' way of tuning the parameters of the junction
- Therefore, encapsulated graphene on intrinsic Silicon with side gate control is a good candidate for RF applications such as qubits [2] and bolometers [3,4]
- MAR features in short ballistic graphene Josephson junctions are not entirely understood

CONTACT PERSON

Guilliam Butseraen

guilliam.butseraen@neel.cnrs.fr

REFERENCES

- [1] L. Wang et al. *Science* **342**, 2013
- [2] J. Wang et al. *Nature Nanotechnology* **14**, 2019
- [3] R. Kokkonen et al. *Nature* **586**, 2020
- [4] G-H. Lee et al. *Nature* **586**, 2020